NCE N-Channel Super Trench Power MOSFET

Description

The NCEP85T25 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification.

General Features

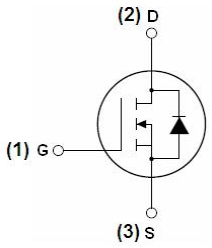
- V_{DS} =85V,I_D =250A
  $R_{DS(ON)}$=2.2mΩ (typical) @ V_{GS}=10V
- Excellent gate charge x $R_{DS(on)}$ product
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

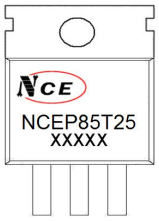
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment

TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP85T25	NCEP85T25	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	85	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	250	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	180	A
Pulsed Drain Current	I_{DM}	1000	A
Maximum Power Dissipation	P_D	300	W
Derating factor		2	W/℃
Single pulse avalanche energy (Note 1)	E_{AS}	2000	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	0.5	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

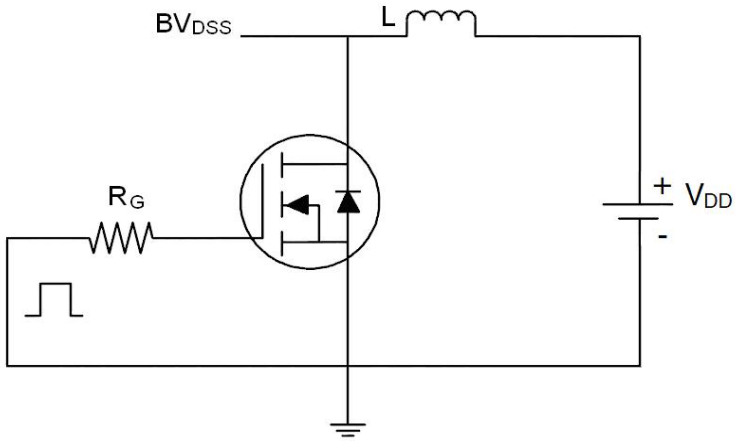
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	85		-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=85V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	2.5	3.5	4.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=100A	-	2.2	2.6	mΩ
Forward Transconductance	g_{FS}	V_{DS}=10V,I_D=100A	-	90	-	S
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=40V,V_{GS}=0V, F=1.0MHz	-	10700	-	PF
Output Capacitance	C_{oss}		-	1700	-	PF
Reverse Transfer Capacitance	C_{rss}		-	76	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=40V,I_D=100A V_{GS}=10V,R_G=1.6Ω	-	28	-	nS
Turn-on Rise Time	t_r		-	73	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	86	-	nS
Turn-Off Fall Time	t_f		-	33	-	nS
Total Gate Charge	Q_g	V_{DS}=40V,I_D=100A, V_{GS}=10V	-	142		nC
Gate-Source Charge	Q_{gs}		-	56		nC
Gate-Drain Charge	Q_{gd}		-	24		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_F= I_S	-		1.2	V
Diode Forward Current	I_S		-	-	250	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F = I_S di/dt = 100A/μs	-	115		nS
Reverse Recovery Charge	Qrr		-	320		nC

Notes:

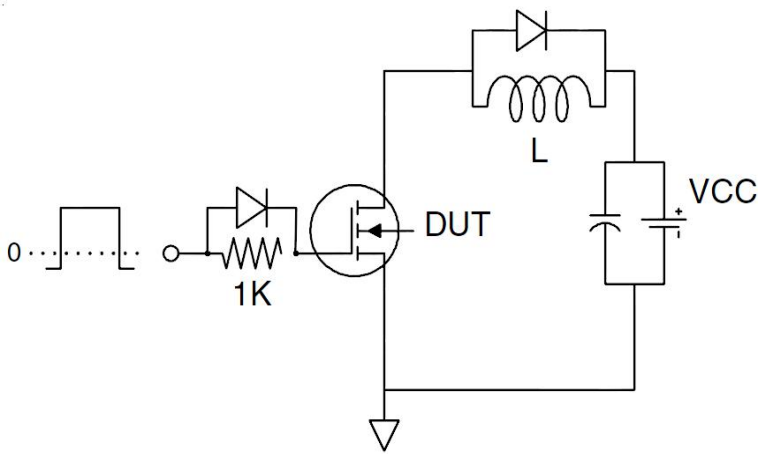
1. EAS condition : Tj=25℃,V_{DD}=40V,V_G=10V,L=0.5mH,Rg=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.

Test Circuit

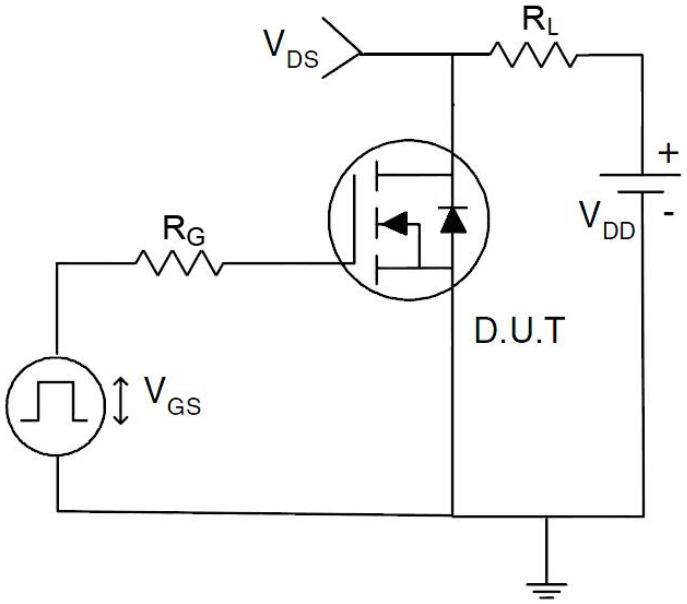
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

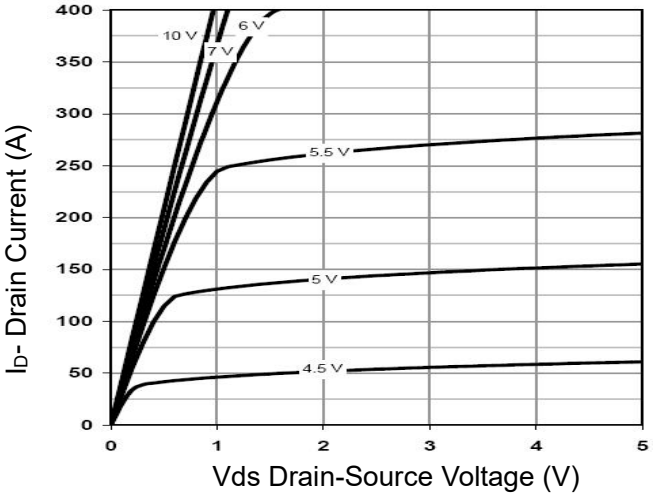


Figure 1 Output Characteristics

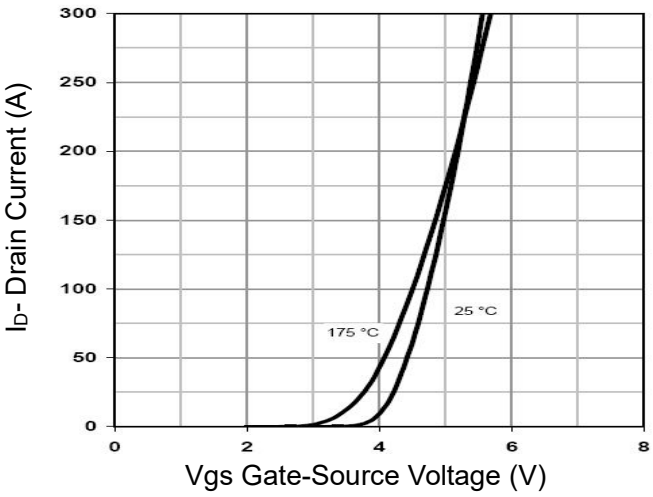


Figure 2 Transfer Characteristics

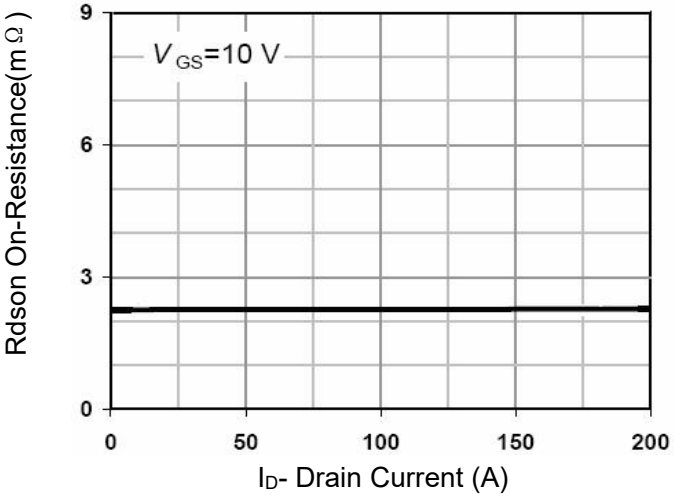


Figure 3 Rdson- Drain Current

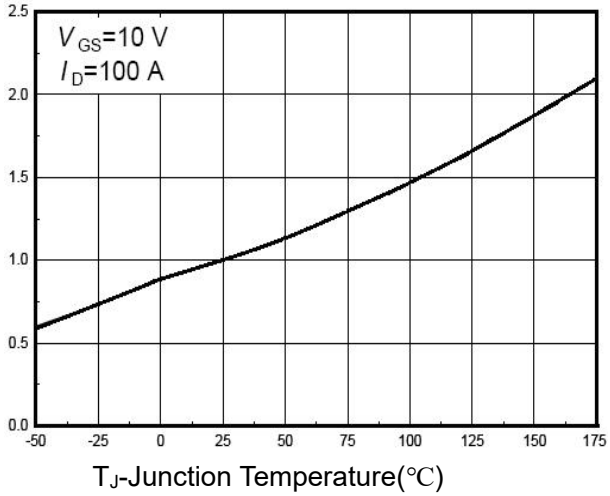


Figure 4 Rdson-JunctionTemperature

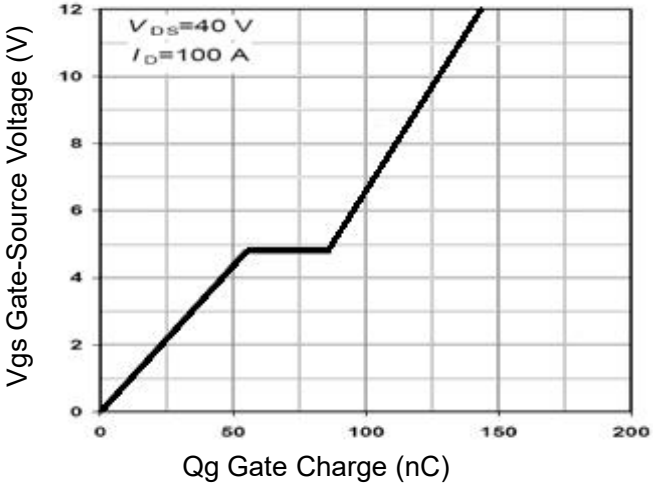


Figure 5 Gate Charge

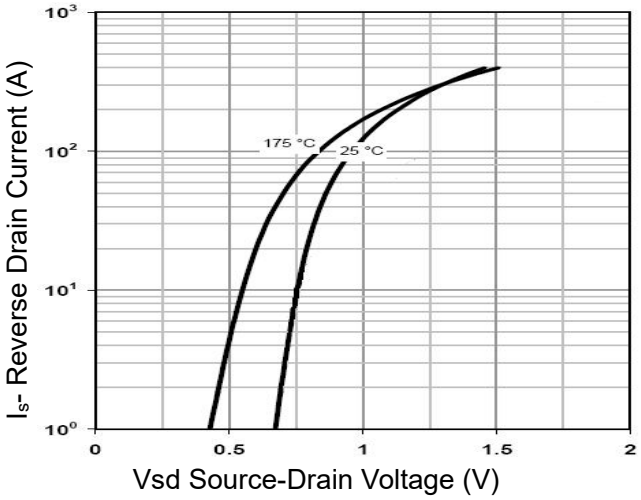


Figure 6 Source- Drain Diode Forward

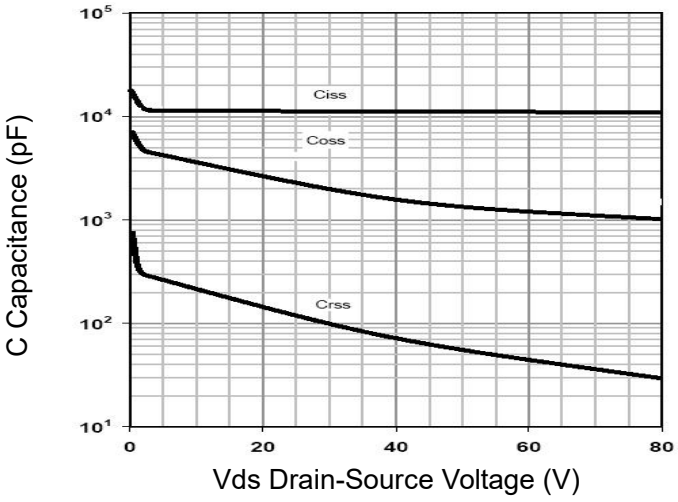


Figure 7 Capacitance vs Vds

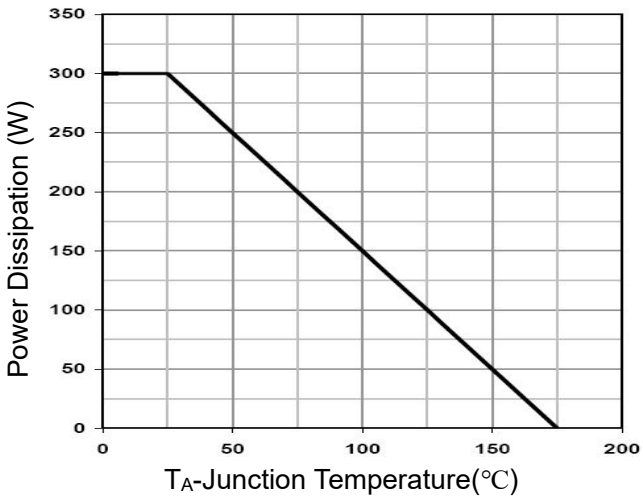


Figure 9 Power De-rating

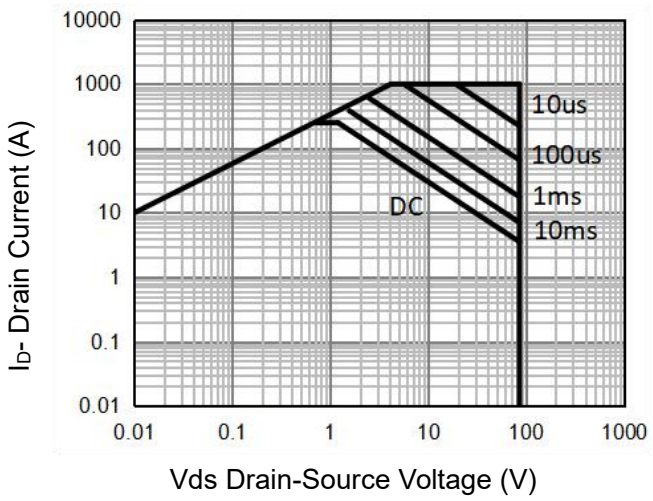


Figure 8 Safe Operation Area(Note 3)

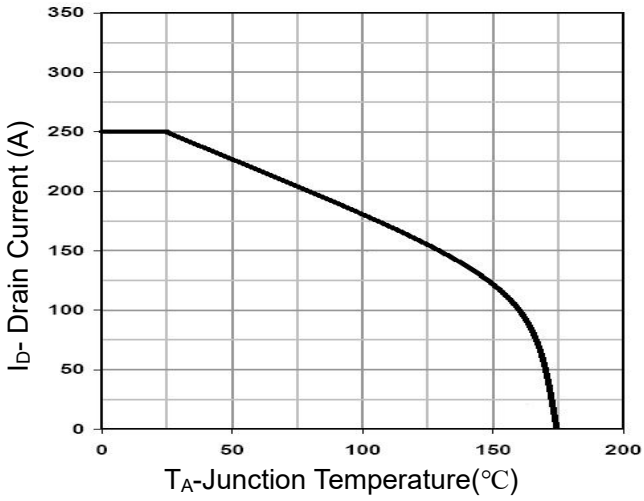


Figure 10 Current De-rating

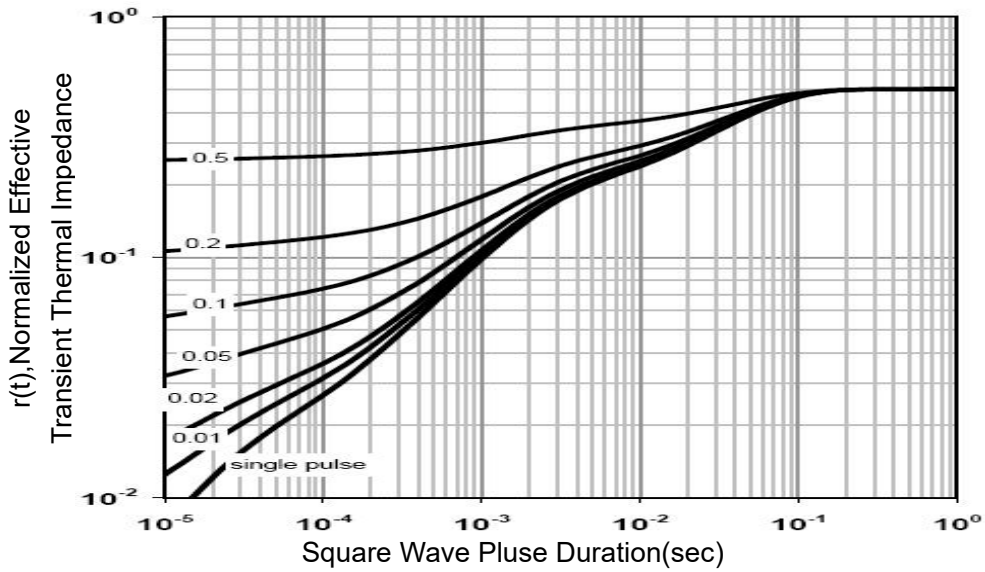
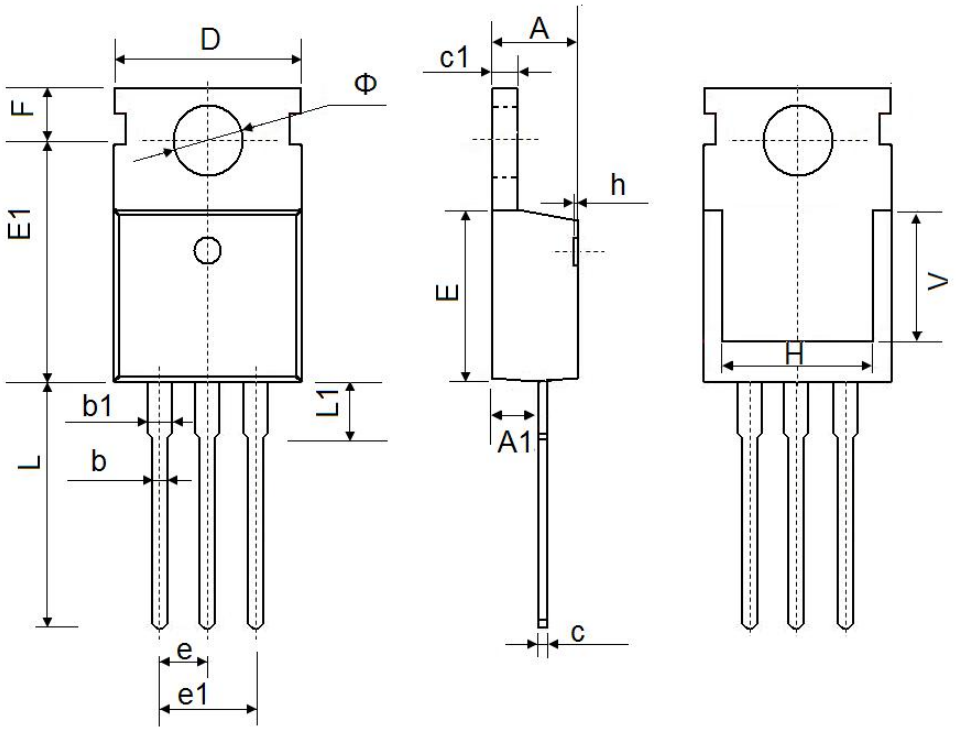


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

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